

BUL89

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- HIGH VOLTAGE CAPABILITY
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- LOW BASE-DRIVE REQUIREMENTS
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C

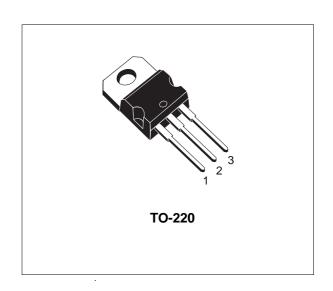
APPLICATIONS

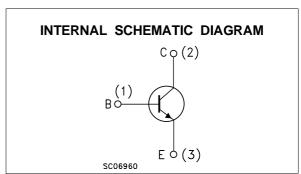
- ELECTRONIC TRANSFORMER FOR HALOGEN LAMPS
- SWITCH MODE POWER SUPPLIES

DESCRIPTION

The BUL89 is manufactured using high voltage Multiepitaxial Mesa technology for cost-effective high performance. It uses a Hollow Emitter structure to enhance switching speeds.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage (V _{BE} = 0)	850	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	400	V
V _{ЕВО}	Emitter-Base Voltage (Ic = 0)	9	V
Ic	Collector Current	12	А
I _{CM}	Collector Peak Current (t _p < 5 ms)	25	Α
I_B	Base Current	6	Α
I _{BM}	Base Peak Current (t _p < 5 ms)	12	Α
P _{tot}	Total Dissipation at T _c = 25 °C	110	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

September 2001 1/6

THERMAL DATA

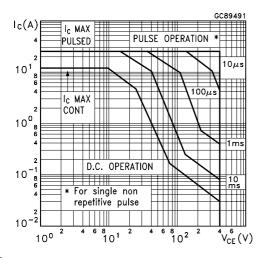
R _{thj-case} Thermal Resistance Junction-Case	Max	1.14	°C/W
--	-----	------	------

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

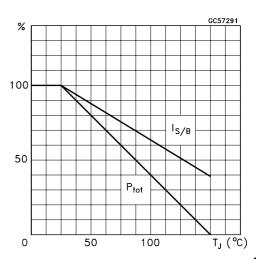
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 850 V V _{CE} = 850 V	T _j = 125 °C			100 500	μA μA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 400 V				100	μΑ
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 10 mA	L = 25 mH	400			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 10 mA		9			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 5 A I _C = 8 A I _C = 12 A	I _B = 1 A I _B = 1.6 A I _B = 2.4 A			1 1.5 5	V V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 5 A I _C = 8 A	I _B = 1 A I _B = 1.6 A			1.3 1.6	V V
h _{FE} *	DC Current Gain	I _C = 5 A I _C = 10 mA	V _{CE} = 5 V V _{CE} = 5 V	10 10		40	
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 8 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $V_{CL} = 350 \text{ V}$ (see figure 1)	I_{B1} = 1.6 A R_{BB} = 0 Ω L = 200 μ H		1.5 55	2.3 110	μs ns
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 8 \text{ A}$ $V_{BE(off)} = -5 \text{ V}$ $V_{CL} = 350 \text{ V}$ $T_{j} = 100 \text{ °C}$	$I_{B1} = 1.6 \text{ A}$ $R_{BB} = 0 \Omega$ $L = 200 \mu\text{H}$ (see figure 1)		1.9 80		μs ns

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area

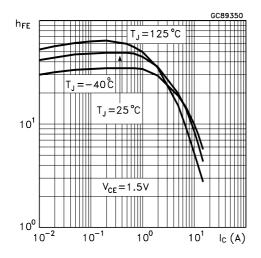


Derating Curve

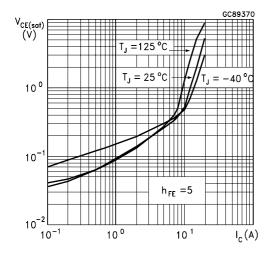


47/

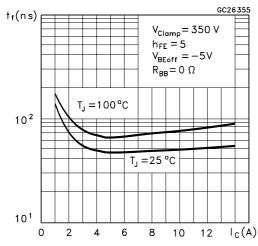
DC Current Gain



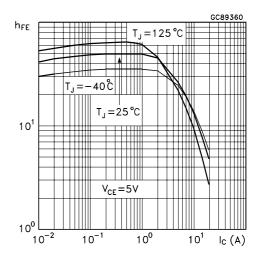
Collector Emitter Saturation Voltage



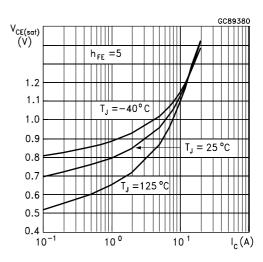
Inductive Load Fall Time



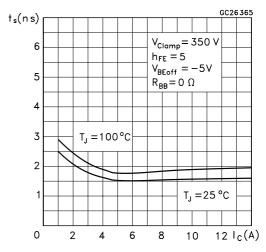
DC Current Gain



Base Emitter Saturation Voltage



Inductive Load Storage Time



4

Reverse Biased SOA

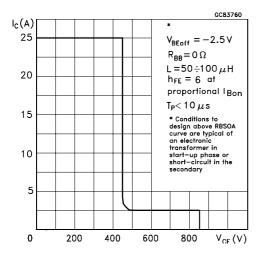
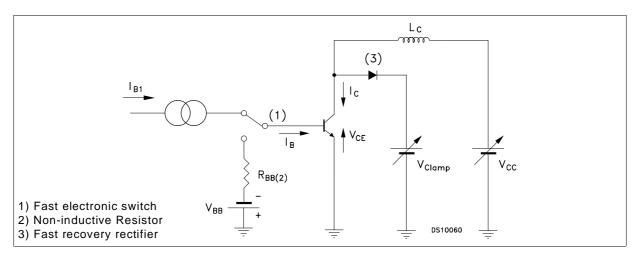


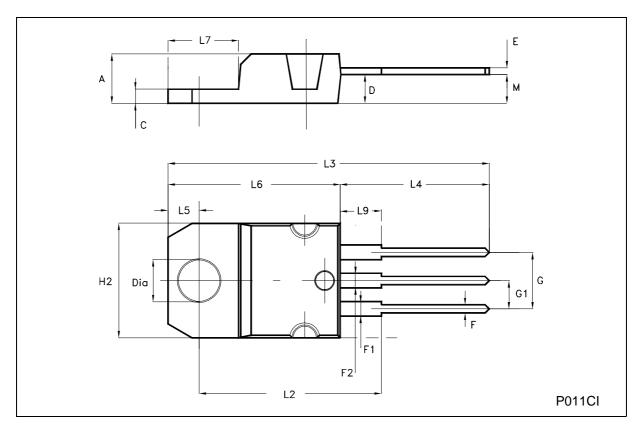
Figure 1: Inductive Load Switching Test Circuit



4/6

TO-220 MECHANICAL DATA

DIM.		mm			inch	
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
Е	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2001 STMicroelectronics – Printed in Italy – All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

77

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by STMicroelectronics manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460
2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM
2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E
US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E
FP204-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G
NTE101 NTE13 NTE15